onsemi

Single-Channel High-Side Gate Drive IC

FAN73611

Description

The FAN73611 is a monolithic high-side gate drive IC that can drive MOSFETs and IGBTs operating up to +600 V. **onsemi**'s high-voltage process and commonmode noise canceling techniques provide stable operation of the high-side driver under high dv/dt noise circumstances. An advanced level-shift circuit offers high-side gate driver operation up to $V_S = -9.8$ V (typical) for $V_{BS} = 15$ V. The UVLO circuits prevents malfunction when V_{DD} or V_{BS} is lower than the specified threshold voltage. The output drivers typically source/sink 250 mA/500 mA; respectively, which is suitable for Plasma Display Panel (PDP) application, motor drive inverter, and switching mode power supply applications.

Features

- Floating Channel of Bootstrap Operation to +600 V
- 250 mA / 500 mA Sourcing/Sinking Current Driving Capability
- Common-Mode dv/dt Noise-Cancelling Circuit
- 3.3 V and 5 V Input Logic Compatible
- Output In Phase with Input Signal
- $\bullet\,$ Under–Voltage Lockout for V_{DD} and V_{BS}
- 8-Lead Small Outline Package (SOP)
- This is a Pb–Free Device

Applications

- Electronic Ballast
- Switching–Mode Power Supply (SMPS)

Related Resources

- <u>AN-6076 Design and Application Guide of Bootstrap Circuit for</u> <u>High-Voltage Gate-Drive IC</u>
- <u>AN-9052 Design Guide for Selection of Bootstrap Components</u>
- <u>AN-8102 Recommendations to Avoid Short Pulse Width Issues</u> in HVIC Gate Driver Applications



(8-SOP) CASE 751EG



ORDERING INFORMATION

See detailed ordering and shipping information on page 11 of this data sheet.

TYPICAL APPLICATION DIAGRAMS





INTERNAL BLOCK DIAGRAM



Figure 2. Functional Block Diagram

PIN CONFIGURATION



Figure 3. Pin Configuration (Top View)

PIN DEFINITIONS

Pin No.	Name	Description
1	V _{DD}	Supply Voltage
2	IN	Logic Input for High-Side Gate Driver Output
3	NC	No Connection
4	GND	Ground
5	NC	No Connection
6	V _S	High-Voltage Floating Supply Return
7	НО	High-Side Driver Output
8	V _B	High-Side Floating Supply

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C, unless otherwise specified.)

Symbol	Parameter	Min	Max	Unit
V _S	High-Side Floating Offset Voltage	V _B – 25	V _B + 0.3	V
VB	High-Side Floating Supply Voltage	-0.3	625.0	V
V _{HO}	High-Side Floating Output Voltage	V _S – 0.3	V _B + 0.3	V
V_{DD}	Low-Side and Logic Supply Voltage	-0.3	25.0	V
V _{IN}	Logic Input Voltage	-0.3	V _{DD} + 0.3	V
dV _S /dt	Allowable Offset Voltage Slew Rate	-	±50	V/ns
PD	Power Dissipation (Notes 1, 2, 3)	-	0.625	W
θ_{JA}	Thermal Resistance	-	200	°C/W
TJ	Junction Temperature	-55	+150	°C
T _{STG}	Storage Temperature	-55	+150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1. Mounted on $76.2 \times 114.3 \times 1.6 \text{ mm PCB}$ (FR-4 glass epoxy material).

2. Refer to the following standards:

JESD51–2: Integral circuits thermal test method environmental conditions, natural convection, and JESD51–3: Low effective thermal conductivity test board for leaded surface mount packages

3. Do not exceed power dissipation (P_D) under any circumstances.

RECOMMENDED OPERATING RATINGS

Symbol	Parameter	Min	Max	Unit
V _B	High-Side Floating Supply Voltage	V _S + 10	V _S + 20	V
V _S	High-Side Floating Supply Offset Voltage	6 – V _{DD}	600	V
V _{HO}	High-Side Output Voltage	V _S	V _B	V
V _{IN}	Logic Input Voltage	GND	V _{DD}	V
V _{DD}	Supply Voltage	10	20	V
T _A	Operating Ambient Temperature	-40	+125	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

ELECTRICAL CHARACTERISTICS (V_{BIAS} (V_{DD} , V_{BS}) = 15.0 V and T_A = 25°C unless otherwise specified. The V_{IN} and I_{IN}
parameters are referenced to GND. The V _O and I _O parameters are relative to V _S and are applicable to the respective outputs HO.)

Symbol	Parameter	Test Condition	Min	Тур	Max	Unit	
POWER SUPPLY SECTION							
I _{QDD}	Quiescent V _{DD} Supply Current	V _{IN} = 0 V or 5 V, C _{LOAD} = 1000 pF	-	80	140	μΑ	
I _{PDD}	Operating V _{DD} Supply Current	C _{LOAD} = 1000 pF, f _{IN} = 20 kHz, RMS value	-	80	160	μΑ	
V_{DDUV+} V_{BSUV+}	V _{DD} and V _{BS} Supply Under-Voltage Positive Going Threshold Voltage	V _{DD} = Sweep, V _{BS} = Sweep	7.8	8.8	9.8	V	
V _{DDUV-} V _{BSUV-}	V _{DD} and V _{BS} Supply Under-Voltage Negative Going Threshold Voltage	V _{DD} = Sweep, V _{BS} = Sweep	7.3	8.3	9.3	V	
V _{DDHYS} V _{BSHYS}	V _{DD} and V _{BS} Supply Under-Voltage Lockout Hysteresis Voltage	V _{DD} = Sweep, V _{BS} = Sweep	-	0.5	-	V	
I _{LK}	Offset Supply Leakage Current	V _B = V _S = 600 V	-	-	10	μΑ	
I _{QBS}	Quiescent V _{BS} Supply Current	V _{IN} = 0 V or 5 V, C _{LOAD} = 1000 pF		60	100	μΑ	
I _{PBS}	Operating V _{BS} Supply Current	C _{LOAD} = 1000 pF, f _{IN} = 20 kHz, RMS value		420	600	μΑ	

INPUT LOGIC SECTION

V _{IH}	Logic "1" Input Voltage		2.5	-	-	V
V _{IL}	Logic "0" Input Voltage		-	-	0.8	V
I _{IN+}	Logic Input High Bias Current	V _{IN} = 5 V	-	50	75	μΑ
I _{IN-}	Logic Input Low Bias Current	V _{IN} = 0 V	-	-	2	μΑ
R _{IN}	Input Pull-Down Resistance		60	100	-	kΩ

GATE DRIVE OUTPUT SECTION

V _{OH}	High Level Output Voltage (V _{BIAS} – V _O)	No Load	-	-	0.1	V
V _{OL}	Low Level Output Voltage	No Load	-	-	0.1	V
I _{O+}	Output High, Short-Circuit Pulsed Current	$\label{eq:VHO} \begin{array}{l} V_{HO} = 0 \ V, \ V_{IN} = 5 \ V, \\ PW \leq 10 \ \mu s \end{array}$	200	250	_	mA
I _{O-}	Output Low, Short-Circuit Pulsed Current	$\label{eq:VHO} \begin{array}{l} V_{HO} = 15 \mbox{ V}, V_{IN} = 0 \mbox{ V}, \\ PW \leq 10 \mu s \end{array}$	400	500	-	mA
Vs	Allowable Negative V _S Pin Voltage for IN Signal Propagation to HO	V _{BS} = 15 V	-	-9.8	-7.0	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

DYNAMIC ELECTRICAL CHARACTERISTICS ($V_{DD} = V_{BS} = 15 \text{ V}$, $C_{LOAD} = 1000 \text{ pF}$, and $T_A = 25^{\circ}C$, unless otherwise specified.)

Symbol	Parameter	Test Condition	Min	Тур	Max	Unit
t _{on}	Turn-on Propagation Delay Time	V _S = 0 V	70	120	170	ns
t _{off}	Turn-off Propagation Delay Time	V _S = 0 V	70	120	170	ns
tr	Turn-on Rise Time		-	70	140	ns
t _f	Turn-off Fall Time		-	30	60	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS







Figure 6. Turn-On Rise Time vs. Temperature



vs. Temperature



Figure 5. Turn-Off Propagation Delay vs. Temperature



Figure 7. Turn-Off Fall Time vs. Temperature





TYPICAL CHARACTERISTICS (Continued)















Figure 11. Operating V_{BS} Supply Current vs. Temperature



Figure 13. V_{DD} UVLO- vs. Temperature



Figure 15. V_{BS} UVLO- vs. Temperature

TYPICAL CHARACTERISTICS (Continued)



TYPICAL CHARACTERISTICS (Continued)





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TYPICAL CHARACTERISTICS (Continued)







Figure 30. Operating V_{DD} Supply Current vs. Supply Voltage



Figure 29. Quiescent V_{BS} Supply Current vs. Supply Voltage



Figure 31. Operating V_{DD} Supply Current vs. Supply Voltage

SWITCHING TIME DEFINITIONS



Figure 32. Switching Time Test Circuit and Waveforms Definitions



Figure 33. Floating Supply Voltage Transient Test

ORDERING INFORMATION

Device	Package	Operating Temperature	Description	Shipping [†]
FAN73611MX (Note 4)	SOIC8 (8–SOP) (Pb–Free)	-40°C∼+125°C	Lightning Application	3000 / Tape & Reel

4. This device has passed wave soldering test by JESD22A-111.

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



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